L Number	Hits	Search Text	DB	Time stamp
6	21	base with (eliminate remov$3) near (hydrogen "h.sub.2") and (438/$6 257/$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:09
7	13	(US-5846869-$ or US-6031255-$ or US-6258685-$ or US-6432788-$ or US-6451659-$ or US-6455390-$ or US-6537838-$ or US-4047976-$ or US-5693541-$).did. or (US-20010026971-$ or US-20020031892-$ or US-20020058399-$ or US-20020187568-$).did.	USPAT; US-PGPUB	2003/10/13 13:09
8	8	(base with (eliminate remov$3) near (hydrogen "h.sub.2") and (438/$6 257/$6)) not ((US-5846869-$ or US-6031255-$ or US-6258685-$ or US-6432788-$ or US-6451659-$ or US-6455390-$ or US-6537838-$ or US-4047976-$ or US-5693541-$).did. or (US-20010026971-$ or US-20020031892-$ or US-20020058399-$ or US-20020187568-$).did.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:10
-	158	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 09:56
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:18
-	52	(((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:57
-	2	("6399971").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:40
-	1	6399971.URPN.	USPAT	2003/10/10 10:38
-	1	"5481120".PN.	USPAT	2003/10/10 10:38
-	2	jp-05326546-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:40
-	0	jp-08-335588-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:41
-	2	jp-05326546-$.did. jp-08335588-$.did. jp-07015357-$.did.	JPO	2003/10/10 10:41
-	1	jp-08335588-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:42
-	2	jp-07015357-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:43

C:\APPS\EAST\Workspaces\10092526.wsp

-	0	jp-0715357-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:43
-	0	jp-70015357-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:56
-	482	(carbon c) near4 (dope doping doped) with base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:12
-	11	(((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped) with base)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:41
-	745	(carbon c) near4 (dope doping doped implant$5) with base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:09
-	745	(carbon c) near4 (dope doping doped implant$5) with base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:12
-	12	(((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped implant$5) with base)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:12
-	1	(((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped implant$5) with base)) not ((((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped) with base))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:13
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:07
-	1238129	(gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga sb as" inassb insbas "in as sb" "in sb as" gainas gainsb ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb") and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:29
-	1003	((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga sb as" inassb insbas "in as sb" "in sb as" gainas gainsb ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:35

-	1002	((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:37
-	37	(((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:42
-	94	(base and emitter and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:42
-	57	((base and emitter and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))) not ((((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 13:42
-	1443	(base and emitter and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 13:42
-	193	(base and emitter and base near (contact and electrode)) and base with ((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:09
-	25	(heat$3 anneal$4) with base with remov$3 near (hydrogen "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:09
-	26	(heat$3 anneal$4) with base with (eliminate remov$3) near (hydrogen "h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:10
-	13	((heat$3 anneal$4) with base with (eliminate remov$3) near (hydrogen "h.sub.2")) and (438/$6 257/$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:10
-	1153	lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:07

C:\APPS\EAST\Workspaces\10092526.wsp

-	645	(lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)) and (438/$6 257/$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:07
-	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:07
-	58	((lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)) and (438/$6 257/$6)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 12:08
-	33	emitter with ((INP "in p") with (algaas gaalas "al ga as" "ga al as"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/13 13:04